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Application No.: 09/650,275  
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PATENT

Sub 1  
A<sup>1</sup> B<sup>1</sup>  
1. (Amended) A die seal structure for a semiconductor die having a  
substrate comprising:  
an elongate region electrically isolated from the remainder of the substrate  
extending around a major portion of the periphery of the substrate and having a gap  
between ends of the elongate region along a minor portion of the periphery; and  
a conductive seal ring extending around the entire periphery of the die in  
direct contact with the die throughout said elongate region in direct contact with and said  
gap to provide a limited electrical connection between the ring and the substrate at said  
gap.

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Sub 2  
A<sup>2</sup> B<sup>2</sup>  
14. (Amended) A die seal structure for a semiconductor die having a  
substrate of a first conductivity type, comprising:  
an elongate well region of a second conductivity type opposite from the  
first conductivity type extending around a major portion of the periphery of the substrate  
and having a gap between the ends of the elongate region along a minor portion of the  
periphery; and  
a conductive seal ring extending around the entire periphery of the die in  
direct contact with the die throughout said elongate well region and in said gap to provide  
a limited electrical connection between the ring and the substrate of said first  
conductivity type at said gap.

Sub 3  
A<sup>3</sup> B<sup>3</sup>  
18. (Amended) A semiconductor device comprising:

- a. a die including a substrate;
- b. a die seal structure on the substrate, the structure comprising:  
an elongate region electrically isolated from the remainder of the  
substrate extending around a major portion of the periphery of the substrate and having a  
gap between ends of the elongate region along a minor portion of the periphery; and